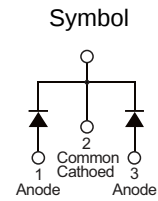


■ PRODUCT CHARACTERISTICS

VR(@IC=0.5mA)	200V
VF(Typ@IF=5A)	0.85V
IR(@VR=200V)	0.05mA
ID	10A

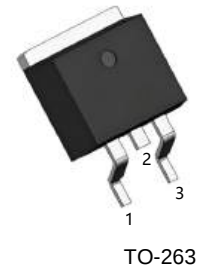


■ MECHANICAL CHARACTERISTICS

- * Case: epoxy,molded
- * Finish:all external surfaces corrosion resistant and terminal
- * Leads are readily solderable
- * Leads temperature for soldering purposes:
260°C Max for 10 seconds

■ FEATURES

- * Low forward voltage
- * Low power loss/high efficiency
- * Low stored charge majority carrier conduction
- * Pb free package are available



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-free	Halogen		
N/A	MBR10200E	TO-263	800pieces/Reel

■ MAXIMUM RATINGS (Each diode leg)

Parameter		Symbol	Value	Unit
Peak repetitive reverse voltage		V _{RRM}	200	V
Average rectified output current	Total	I _O	10	A
	Per leg		5	A
Non-repetitive peak forward surge current 8.3ms single half sine-wave superimposed on reate load		I _{FSM}	150	A
Operating and storage temperature range		T _J ,T _{STG}	-55 to + 175	°C

■ ELECTRICAL CHARACTERISTICS(T_A=25°C Unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Peak repetitive reverse voltage	B _V	I _C =0.5mA, T _J =25°C	200	-	-	V
Forward voltage drop	V _F	I _F =5A, T _J =25°C	-	0.85	0.9	V
Typical junction capacitance per diode	C _J	V _R =4V,f=1MHz	-	105	-	pF
Leakage current	I _R	V _R =200V, T _J =25°C	-	-	0.05	mA
		V _R =200V,T _J =125°C	-	-	20	
Typical thermal resistance per diode	R _{θJ-A}		-	50	-	°C/W
	R _{θJ-C}		-	2	-	

■ TYPICAL CHARACTERISTICS

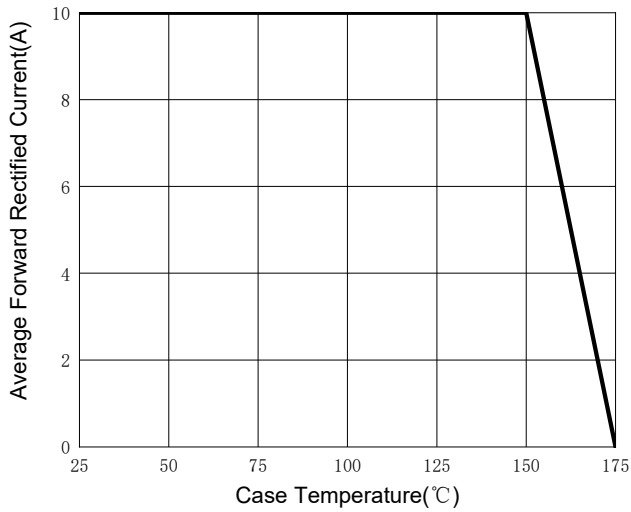


Fig.1: Forward Current Derating Curve

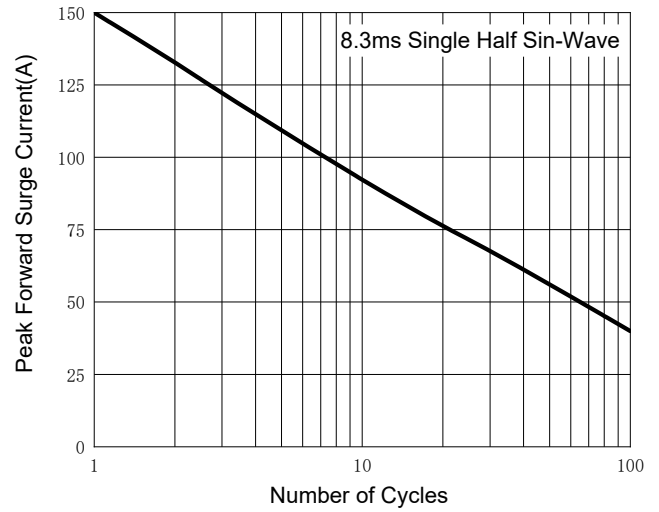


Fig.2: Forward Surge Current Capability (Per Diode)

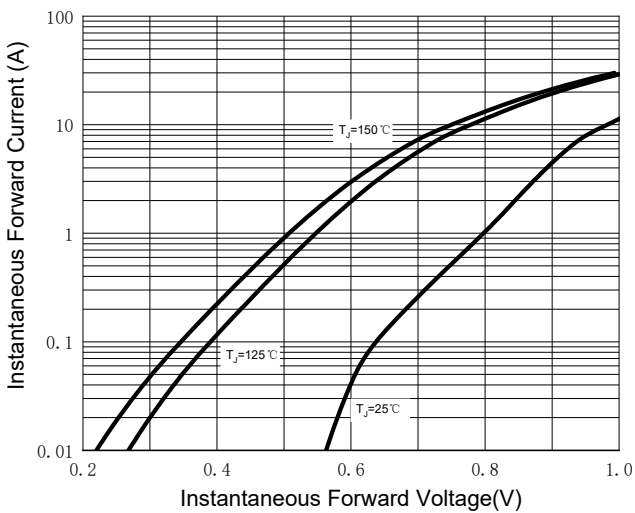


Fig.3: Typical Instantaneous Forward Characteristics (Per Diode)

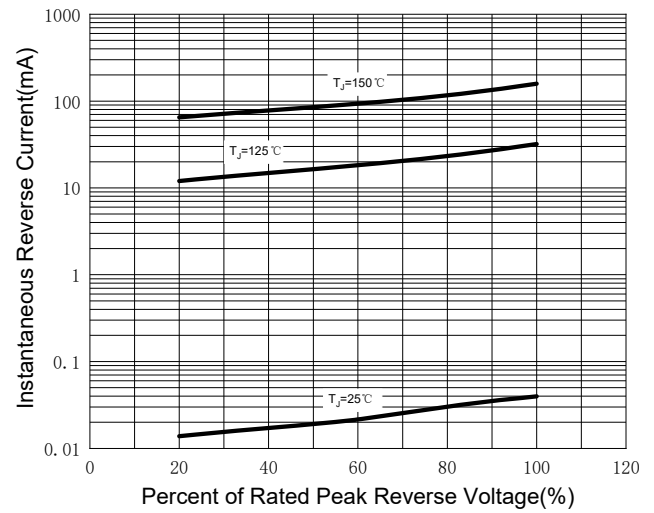


Fig.4: Typical Reverse Leakage Characteristics (Per Diode)

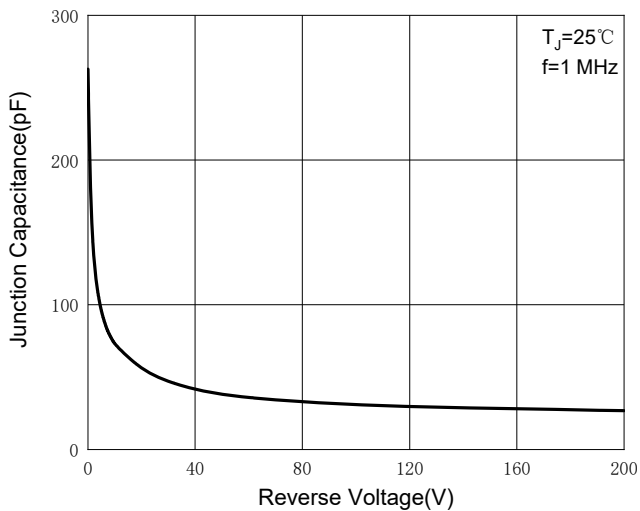


Fig.5: Typical Junction Capacitance (Per Diode)

■ TO-263 PACKAGE OUTLINE DIMENSIONS
